

ATTY. DKT. No.:
U.S. SERIAL No.:
FILED:
APPLICANT:
TITLE:

INVENTOR:
EXPRESS MAIL No.:

INFN/0037
UNKNOWN
HEREWITH
INFINEON TECHNOLOGIES, AG
DRAM CELL ARRANGEMENT WTH VERTICAL MOS
TRANSISTORS, AND METHOD FOR ITS FABRICATION
SCHLÖSSER, ET AL
EV335472255US

CONF. No.: UNKNOWN

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FIG 1b

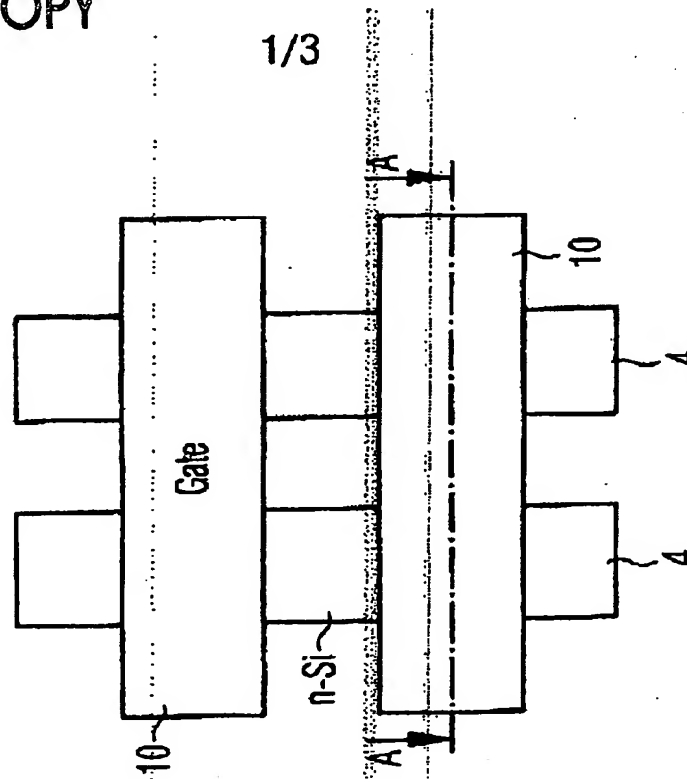
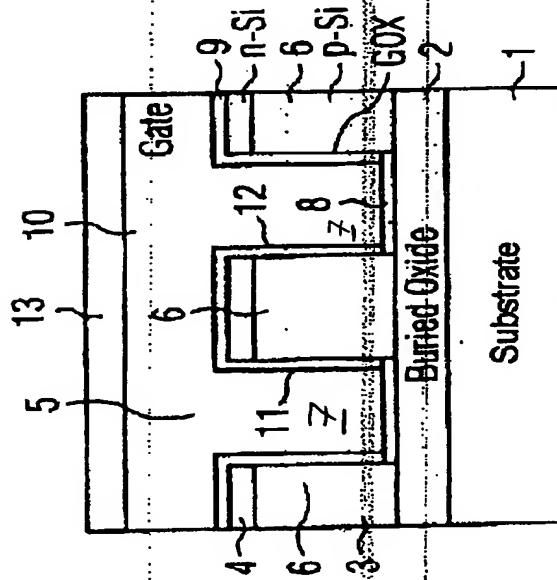


FIG 1a



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FIG 2C

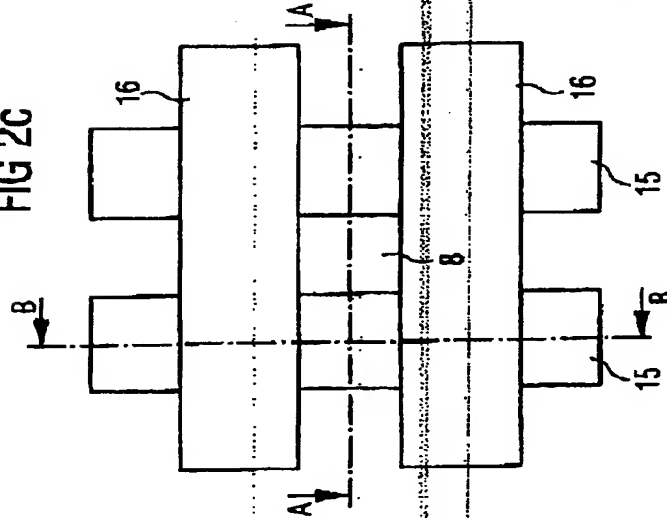


FIG 2a

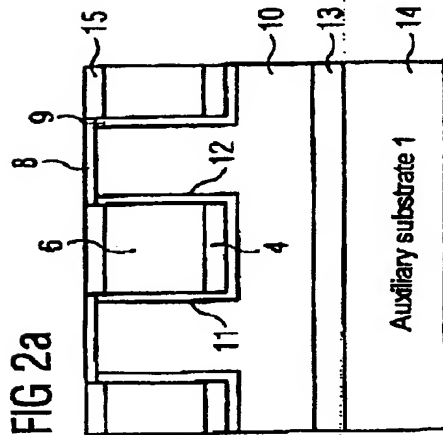
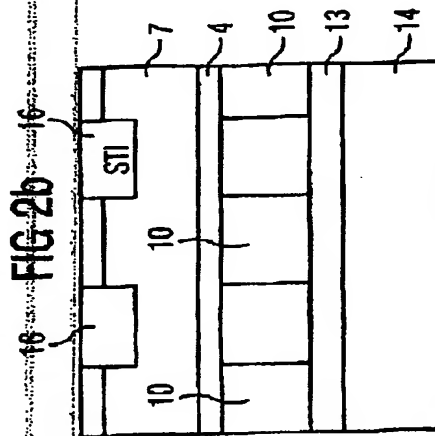


FIG 2b



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FIG 4

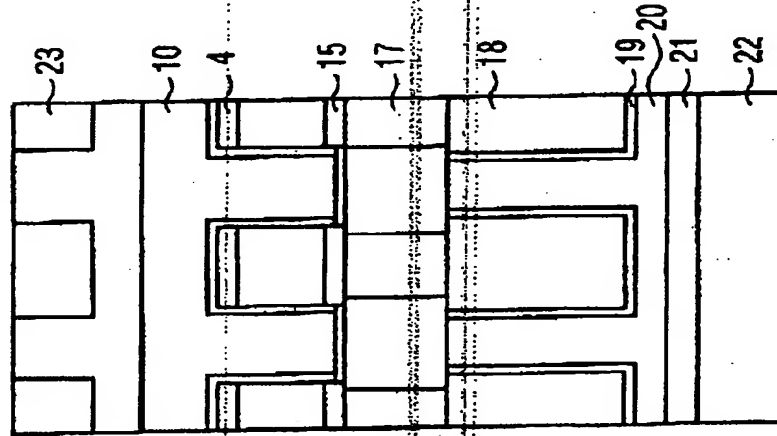


FIG 3

